/	1	•	
$\mathcal{E}_{\mathcal{J}}$	1		
P	5		introducing a second agent comprising hydrogen peroxide [onto the] to a
	6	<u>metal</u>	[layer] plug.
\$\frac{1}{2}	z.b	9	(Amended) A method of removing at least one particle from a portion of a
	7/22	metal	layer on a substrate comprising:
	(3)		depositing a slurry onto the substrate;
	4		polishing the metal layer and the substrate; and
	5		rinsing [the substrate] a metal plug with a solution comprising hydrogen
	6	perox	ide.
t.		•	
	1	12.	(Amended) The method of claim 9, wherein rinsing the [substrate] metal
٠	2	plug (	occurs after polishing the metal layer and substrate.
X	1	13.	(Amended) The method of claim 9, wherein rinsing the [substrate] metal
	2	plug (	comprises rinsing with the solution which comprises approximately 4% by
	3	volun	ne or less of hydrogen peroxide.
,	V2-	)	
50	'3' /	14.	The method of claim 9, wherein polishing the metal layer includes removing
_	*2(	the m	uetal
		<del>\</del>	
	(3)	187	(Amended) A method of polishing a metal layer on a substrate comprising:
5	7/2/	$\langle  $	polishing the metal layer and introducing a rinsing solution onto [the] a
7		metal	[layer] plug, the rinsing solution comprising hydrogen peroxide.
	1	19.	(Amended) The method of claim 18, further including polishing the
	2	[subst	rate] metal layer with an abrasive material, wherein the rinsing solution is
	3	introc	luced after a polishing of the substrate.
7	\( \frac{\frac{1}{2}}{2} \) \( \frac{1}{2} \) \( \frac{3}{2} \)	metal 19. [subst	polishing the metal layer and introducing a rinsing solution onto [the] a [layer] plug, the rinsing solution comprising hydrogen peroxide.  (Amended) The method of claim 18, further including polishing the rate] metal layer with an abrasive material, wherein the rinsing solution is